

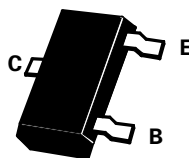
# SOT23 PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

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## BCX17

PARTMARKING DETAILS – BCX17 – T1  
BCX17R – T4

COMPLIMENTARY TYPES - BCX19



SOT23

### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Emitter Voltage	$V_{CES}$	-50	V
Collector-Emitter Voltage ( $I_C = -10\text{mA}$ )	$V_{CEO}$	-45	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-500	mA
Peak Collector Current	$I_{CM}$	-1000	mA
Peak Emitter Current	$I_{EM}$	-1000	mA
Base Current	$I_B$	-100	mA
Peak Base Current	$I_{BM}$	-200	mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	$P_{tot}$	330	mW
Operating and Storage Temperature Range	$T_J:T_{stg}$	-55 to +150	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Cut-Off Current	$I_{CBO}$			-100 -200	nA $\mu\text{A}$	$I_E = 0, V_{CB} = -20\text{V}$ $I_E = 0, V_{CB} = -20\text{V}, T_J = 150^\circ\text{C}$
Emitter-Base Cut-Off Current	$I_{EBO}$			-10	$\mu\text{A}$	$I_C = 0, V_{EB} = -1\text{V}$
Base-Emitter Voltage	$V_{BE}$			-1.2	V	$I_C = -500\text{mA}, V_{CE} = -1\text{V}^*$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-620	mV	$I_C = -500\text{mA}, I_B = -50\text{mA}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	100 70 40		600		$I_C = -100\text{mA}, V_{CE} = -1\text{V}$ $I_C = -300\text{mA}, V_{CE} = -1\text{V}^*$ $I_C = -500\text{mA}, V_{CE} = -1\text{V}^*$
Transition Frequency	$f_T$		100		MHz	$I_C = -10\text{mA}, V_{CE} = -5\text{V}$ $f = 35\text{MHz}$
Output Capacitance	$C_{obo}$		8.0		pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$

\*Measured under pulsed conditions.

Spice parameter data is available upon request for this device